



YJQ40G10AQ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

| | |
|----------------------------|------|
| V_{DS} | 100V |
| I_D | 40A |
| $R_{DS(ON)}$ (at V_{GS} | |

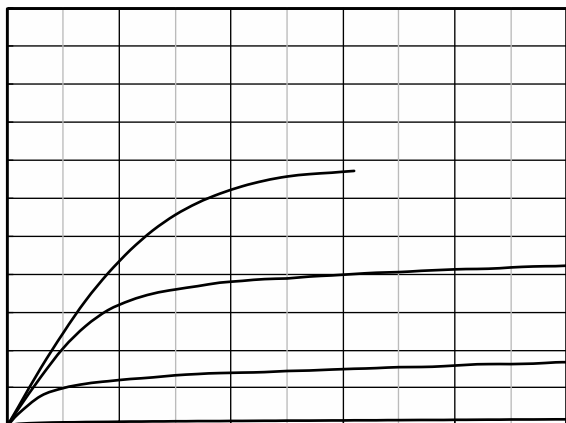
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Electrical Characteristics ($T_J=25$ unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max |
|-----------|--------|------------|-----|-----|-----|
|-----------|--------|------------|-----|-----|-----|

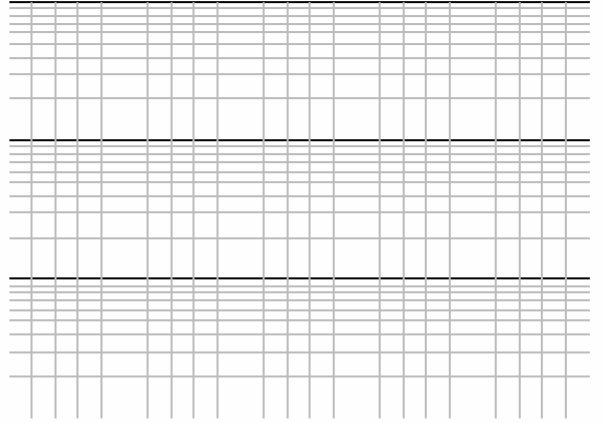
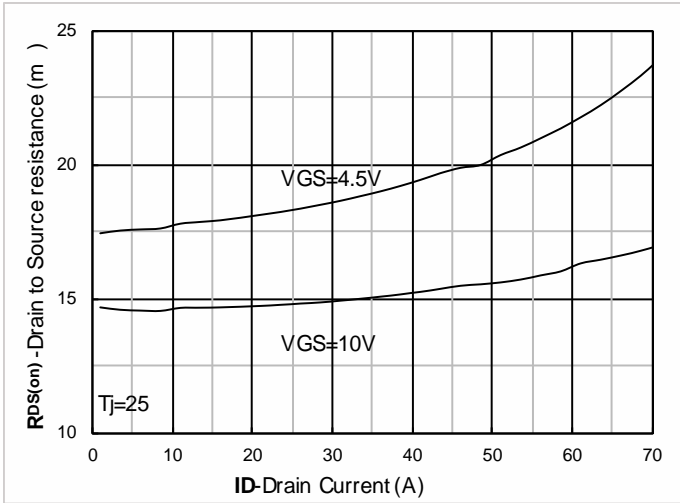


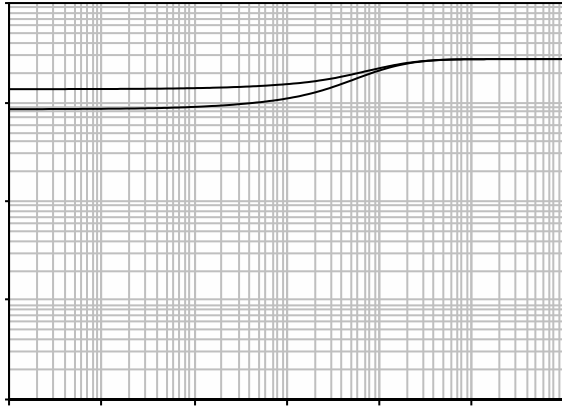
Typical Electrical and Thermal Characteristics Diagrams





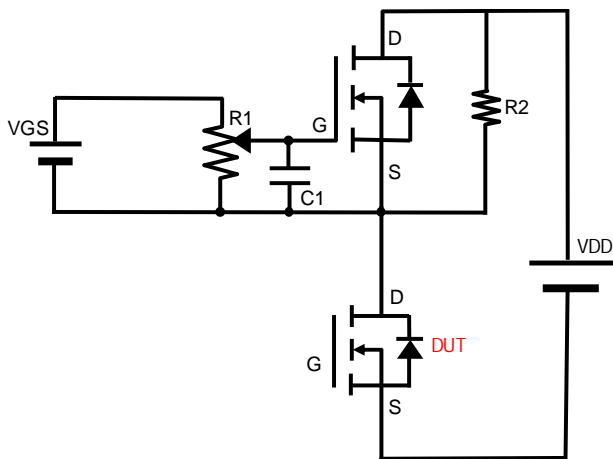
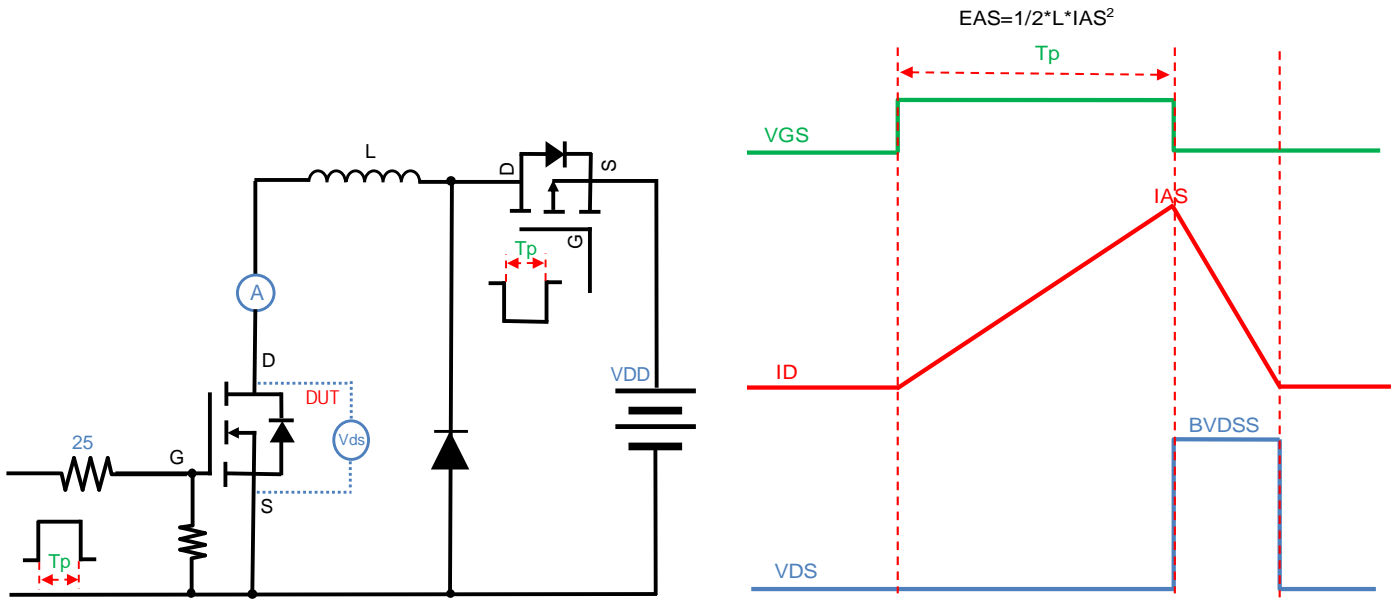
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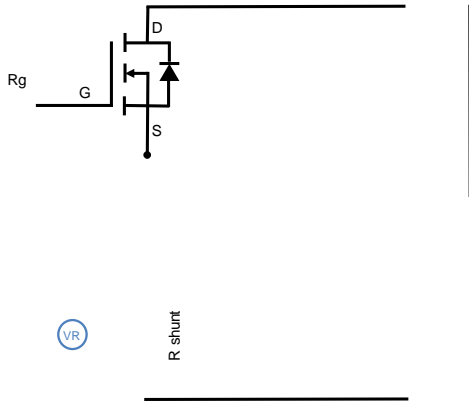


Test Circuits & Waveforms





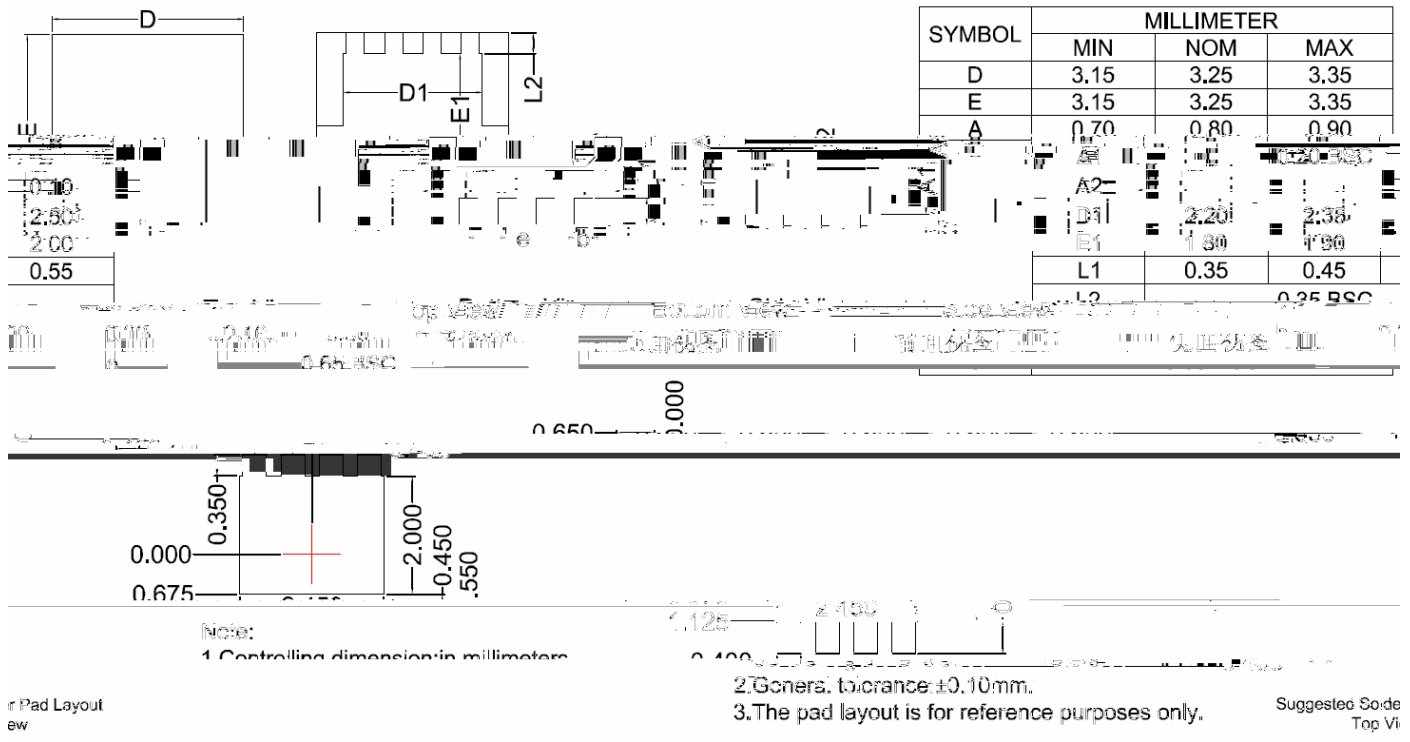
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DFN3333-8L Package information





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